

Description

The XE9DHC5VU is a ESD protection diode which provide a very high level protection for sensitive electronic components that may be subjected to electrostatic discharge (ESD). It is designed to replace multilayer varistors (MLV) in consumer equipments applications such as mobile phone, notebook, PAD, STB, LCD TV etc.

The XE9DHC5VU may be used to provide ESD protection up to ±30kV (contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 7.5A (8/20µs) according to IEC61000-4-5.

The XE9DHC5VU is available in SOD923 package. Standard products are Pb-free and Halogen-free.

Features

- Working voltage: 5V
- ◆ SOD923 Package
- ◆ IEC 61000-4-2 (ESD) ±30kV (air),

 \pm 30kV (contact)

- ◆ IEC 61000-4-5 (Surge) 7.5A (8/20us)
- Low leakage current
- ◆ Low clamping voltage
- Solid-state silicon-avalanche technology

http//:www.xihangsemi.com



SOD923



Circuit Diagram



Marking (Top View)

Order Information

Device	Package	Shipping
XE9DHC5VU	SOD923	8000/Tape&Reel

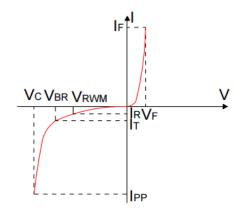
Applications

- Personal digital assistants (PDA's)
- Notebooks, Desktops, and Servers
- Cell phone Handsets and Accessories
- Portable Electronics
- Peripherals



Definitions of electrical characteristics

Symbol	Parameter			
V_{RWM}	Reverse Stand-off Voltage			
I _R	Reverse Leakage Current @ V _{RWM}			
V_{BR}	Reverse Breakdown Voltage @ I_T			
I _R	Reverse Breakdown Current			
I _{PP}	Reverse Peak Pulse Current			
V _C	Clamping Voltage @ I _{PP}			
V_{F}	Forward Voltage			



Absolute Maximum Rating

Rating	Symbol	Value	Units	
Peak Pulse Power (t _P = 8/20µS)	P _{PK}	92	W	
Peak Pulse Currentr ($t_P = 8/20 \mu S$)	l _{pp}	7.5	Α	
ESD according to IEC61000-4-2 air discharge	V	±30	kV	
ESD according to IEC61000-4-2 contact discharge	V_{ESD}	±30	kV	
Lead Soldering Temperature	T_L	260 (10 sec)	°C	
Operating Temperature	T_OP	150	°C	
Storage Temperature	T _{STG}	-55 to +150	°C	

Electrical Characteristics (Ta=25℃, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				5	٧
Reverse Leakage Current	I _R	V _{RWM} =5V			1	uA
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	6.2			V
Forward Voltage	V_{F}	I _F = 10mA			0.9	٧
Clamping Voltage(1)	V _C	I_{PP} =7.5A t_P = 8/20 μ s			12.3	V
Junction Capacitance	C _j	V _R =0V f = 1MHz		40		pF

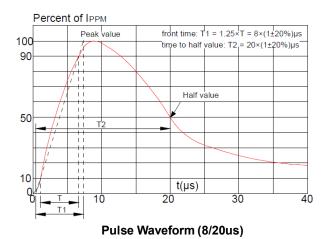
Notes:

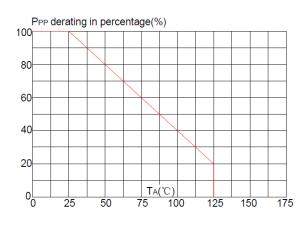
(1)Non-repetitive current pulse, according to IEC61000-4-5.

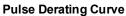
Rev.1.0 2 www.xihangsemi.com

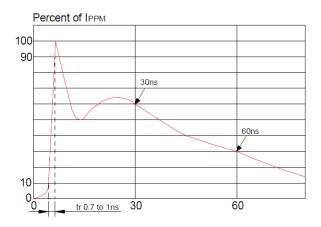


Typical Characteristics (Ta=25℃, unless otherwise noted)







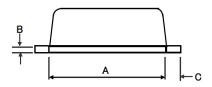


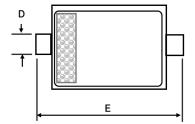
ESD Clamping(8kV Contact Discharge)

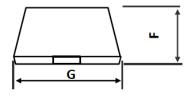
Rev.1.0 3 www.xihangsemi.com



Package Outline Dimensions: (SOD923)





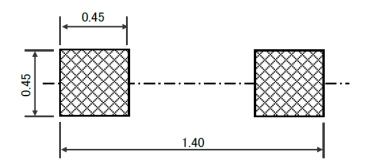


Unit	Α	В	С	D	Е	F	G
Max.	0.90	0.20	0.15	0.30	1.10	0.45	0.65
Min.	0.70	0.05	0.05	0.15	0.90	0.39	0.55

Note:

- 1.Halogen free,EMC
- 2.Pb free solder
- 3.Lead thickness includes solder plating
- 4.Lead frame: Cu
- 5.Other Tolerance: ±0.05
- 6.Dimensions are exclusive of Burrs, Mold Flash and Tie Bar extrusions
- 7.Unit: mm

Land Pattern Recommendation



Note:

This recommended land pattern is for reference purpose only.

NOTICE

XIHANG's products are not authorized for use as components in any life support device or systems.

XIHANG reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. XIHANG does not assume any liability arising out of the application or use of any product described herein.